

zeta potential of said inorganic particles are of opposite signs, and said polymer particles and said inorganic particles are electrostatically bonded to form composite particles, and

a plurality of said inorganic particles are attached to a surface of said polymer particles, and a ratio (S_p/S_i) of a mean particle size of said polymer particles (S_p) and a mean particle size of said inorganic particles (S_i) is from 1 to 40.

Sub 28 > 45. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 44, wherein a ratio (S_p/S_i) of a mean particle size of said polymer particles (S_p) and a mean particle size of said inorganic particles (S_i) is from 1.5 to 20.

46. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 44, wherein a ratio (W_p/W_i) of a content of said polymer particles (W_p) and a content of said inorganic particles (W_i) is from 0.05 to 1.

47. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 44, wherein said polymer particles have at least one functional group selected from the group consisting of carboxyl groups, anions of carboxyl groups, sulfonic acid groups and anions of sulfonic acid groups, and said inorganic particles are alumina, titania, or combinations thereof.

48. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 47, wherein said inorganic particles are alumina, and the pH of said aqueous dispersion is from 2 to 9.

49. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 47, wherein said inorganic particles are titania, and the pH of said aqueous dispersion is from 2 to 6.

50. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 44, wherein said polymer particles have at least one functional group selected from the group consisting of cation-formable nitrogen-containing groups and cations of cation-formable nitrogen-containing groups, and at least one of said inorganic particles is selected from the group consisting of silica, zirconia and titania.

51. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 50, wherein said inorganic particles are silica, and the pH of said aqueous dispersion is from 2.5 to 8.5.

52. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 50, wherein said inorganic particles are zirconia, and the pH of said aqueous dispersion is from 4 to 8.5.

53. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 50, wherein said inorganic particles are titania, and the pH of said aqueous dispersion is from 6.5 to 8.5.

54. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 47, 48 or 49, wherein said polymer particles have at least one functional group selected from the group consisting of ester groups, amide groups, hydroxyl groups, and ether groups.

55. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 44, further comprising a surfactant, wherein a content of said surfactant is not greater than 0.15 wt%.

56. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 55, further comprising an oxidizing agent, a polyvalent metal ion, or combinations thereof.

57. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 56, further comprising an organic acid.

58. (New) An aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices, said dispersion comprising polymer particles, inorganic particles and water, wherein the zeta potential of said polymer particles and the zeta potential of said inorganic particles are of opposite signs, said polymer particles and said inorganic particles are electrostatically bonded to form composite particles, and a plurality of said inorganic particles are attached to a surface of said polymer particles, and a ratio (Sp/Si) of a mean particle size of said polymer particles (Sp) and a mean particle size of said inorganic particles (Si) is from 1 to 40, said composite particles are obtained after ultrasonic irradiation treatment or mechanical shear stress treatment with a homogenizer, and a mean particle size of said composite particles is not greater than $1\mu\text{m}$.

59. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 58, wherein said polymer particles have at least one functional group selected from the group consisting of carboxyl groups, anions of carboxyl groups, sulfonic acid groups and anions of sulfonic acid groups, and said inorganic particles are alumina or titania.

60. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 58, wherein said polymer particles have at least one functional group selected from the group consisting of cation-formable

nitrogen-containing groups and cations of cation-formable nitrogen-containing groups, and said inorganic particles are selected from the group consisting of silica, zirconia and titania.

61. (New) An aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices, said dispersion comprising polymer particles, inorganic particles and water, wherein the zeta potential of said polymer particles and the zeta potential of said inorganic particles are of opposite signs, and said polymer particles and said inorganic particles are electrostatically bonded to form composite particles, and a plurality of said inorganic particles are attached to a surface of said polymer particles, and a ratio (W_p/W_i) of a content of said polymer particles (W_p) and a content of said inorganic particles (W_i) is from 0.05 to 1.

62. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 61, wherein said polymer particles have at least one functional group selected from the group consisting of carboxyl groups, anions of carboxyl groups, sulfonic acid groups and anions of sulfonic acid groups, and said inorganic particles are alumina, titania or combinations thereof.

63. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 62, wherein said inorganic particles are alumina, and the pH of said aqueous dispersion is from 2 to 9.

64. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 62, wherein said inorganic particles are titania, and the pH of said aqueous dispersion is from 2 to 6.

65. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 62, wherein said polymer particles have at least one functional group selected from the group consisting of cation-formable

nitrogen-containing groups, cations of cation-formable nitrogen-containing groups and combinations thereof, and said inorganic particles are selected from the group consisting of silica, zirconia and titania.

66. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 65, wherein said inorganic particles are silica, and the pH of said aqueous dispersion is from 2.5 to 8.5.

67. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 65, wherein said inorganic particles are zirconia, and the pH of said aqueous dispersion is from 4 to 8.5.

68. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 65, wherein said inorganic particles are titania, and the pH of said aqueous dispersion is from 6.5 to 8.5.

69. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 62, 63, or 64, wherein said polymer particles have at least one functional group selected from the group consisting of ester groups, amide groups, hydroxyl groups, and ether groups.

70. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 61, further comprising a surfactant, wherein a content of said surfactant is not greater than 0.15 wt%.

71. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 70, further comprising an oxidizing agent, a polyvalent metal ion or combinations thereof.

72. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 71, further comprising an organic acid.

73. (New) An aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices, said dispersion comprising polymer particles, inorganic particles and water, wherein the zeta potential of said polymer particles and the zeta potential of said inorganic particles are of opposite signs, said polymer particles and said inorganic particles are electrostatically bonded to form composite particles, and a plurality of said inorganic particles are attached to a surface of said polymer particles, and a ratio (W_p/W_i) of a content of said polymer particles (W_p) and a content of said inorganic particles (W_i) is from 0.05 to 1, said composite particles are obtained after ultrasonic irradiation treatment or mechanical shear stress treatment with a homogenizer, and a mean particle size of said composite particles is not greater than $1\ \mu\text{m}$.

74. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 73, wherein said polymer particles have at least one functional group selected from the group consisting of carboxyl groups, anions of carboxyl groups, sulfonic acid groups and anions of sulfonic acid groups, and said inorganic particles are alumina or titania.

75. (New) The aqueous dispersion for chemical mechanical polishing used in the manufacture of semiconductor devices according to Claim 73, wherein said polymer particles have at least one functional group selected from the group consisting of cation-formable nitrogen-containing groups and cations of cation-formable nitrogen-containing groups, and said inorganic particles are selected from the group consisting of silica, zirconia, titania and combinations thereof.